



BYW100-200

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODE

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1.5 A
V_{RRM}	200 V
$T_j(\text{max})$	150 °C
$V_F(\text{max})$	0.85 V

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- The specifications and curves enable the determination of t_{rr} and I_{RM} at 100°C under users conditions.

DESCRIPTION

Low voltage drop and rectifier suited for switching mode base drive and transistor circuits.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V
I_{FRM}	Repetitive peak forward current *	$t_p = 5\mu s \quad F = 1\text{KHz}$	A
$I_{F(AV)}$	Average forward current*	$T_a = 95^\circ\text{C} \quad \delta = 0.5$	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms} \quad \text{Sinusoidal}$	A
T_{stg}	Storage temperature range	-65 +150	°C
T_j	Maximum operating junction temperature	+ 150	°C
T_L	Maximum lead temperature for soldering during 10s at 4mm from case	230	°C

* On infinite heatsink with 10mm lead length

BYW100-200

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient*	45	°C/W

* On infinite heatsink with 10mm lead length.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			10	μA
		$T_j = 100^\circ\text{C}$				0.5	mA
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 4.5\text{A}$			1.2	V
		$T_j = 100^\circ\text{C}$	$I_F = 1.5\text{A}$		0.78	0.85	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.75 \times I_{F(AV)} + 0.075 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions		Min.	Typ.	Max.	Unit
t_{rr}	$I_F = 1\text{A}$	$di_F/dt = -50\text{A}/\mu\text{s}$ $V_R = 30\text{V}$			35	ns
t_{fr}	$I_F = 1.5\text{A}$	$di_F/dt = -50\text{A}/\mu\text{s}$ Measured at $1.1 \times V_{Fmax}$		30		ns
V_{FP}	$I_F = 1.5\text{A}$	$di_F/dt = -50\text{A}/\mu\text{s}$		5		V
Q_{rr}	$I_F = 1.5\text{A}$	$di_F/dt = -20\text{A}/\mu\text{s}$ $V_R \leq 30\text{V}$		10		nC

Fig. 1: Average forward power dissipation versus average forward current.

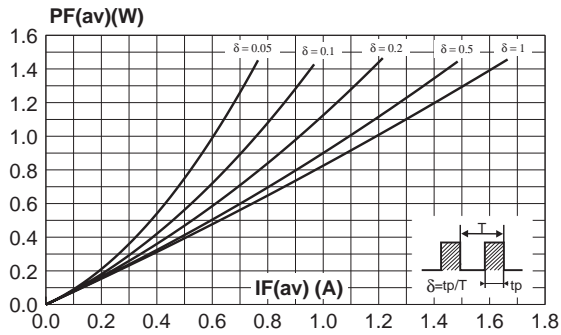


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

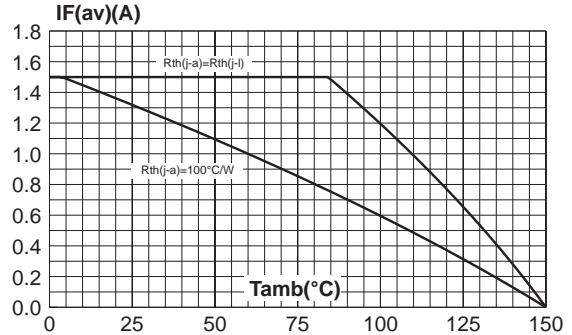


Fig. 3: Thermal resistance versus lead length.

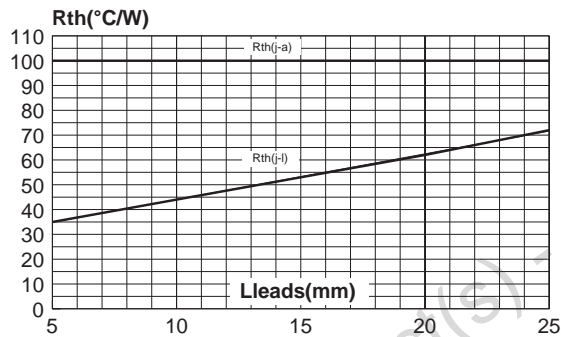


Fig. 4: Variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, epoxy FR4, e(Cu) = 35µm).

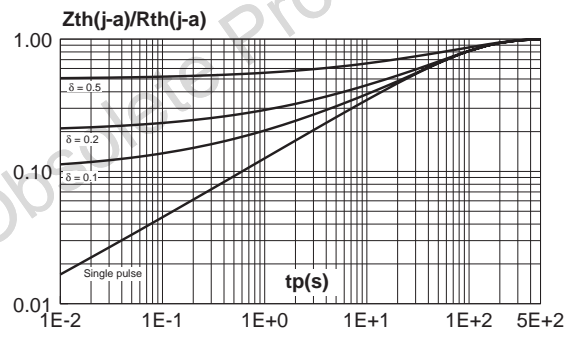


Fig. 5: Forward voltage drop versus forward current (maximum values).

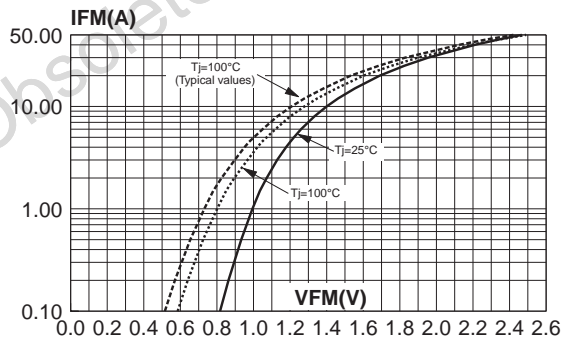


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

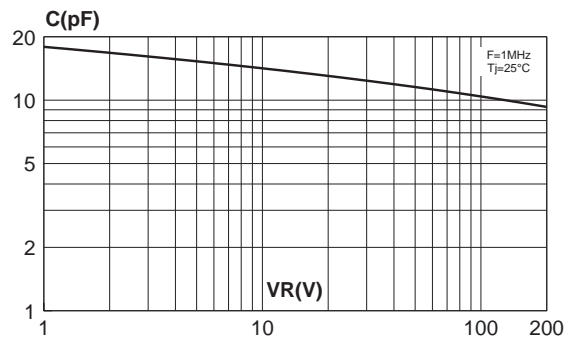


Fig. 7: Reverse recovery time versus di_F/dt .

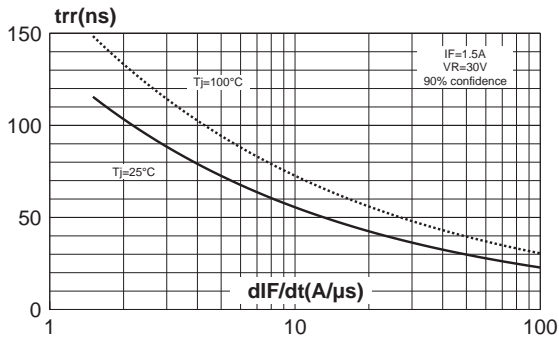


Fig. 8: Peak reverse recovery current versus di_F/dt .

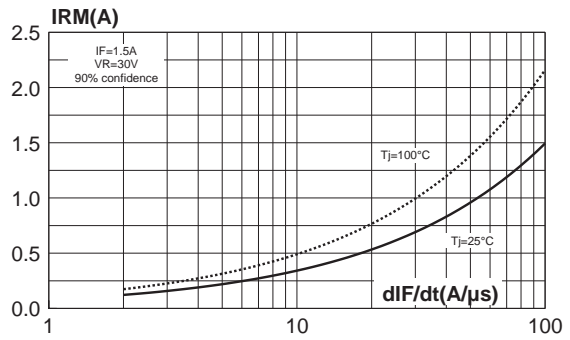
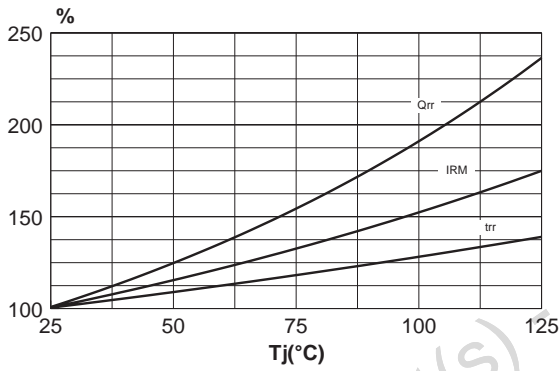


Fig. 9: Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
DO-15

	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
	A	6.05	6.75	0.238
B	2.95	3.53	0.116	0.139
C	26	31	1.024	1.220
D	0.71	0.88	0.028	0.035

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW100-200	BYW100-200	DO-15	0.4 g	1000	Ammopack
BYW100-200RL	BYW100-200	DO-15	0.4 g	6000	Tape and reel

- White band indicates cathode
- Epoxy meets UL 94,V0

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
 Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>

